

N-Channel 30 V (D-S) Power MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}$ (m Ω)	I _D (A)		
30	19 at V _{GS} = 10 V	7.2		
30	23 at V _{GS} = 4.5 V	1.2		

FEATURES

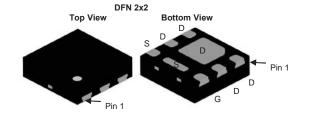
- DT-Trench Power MOSFET
- Ultra Small DFN2X2 Chipscale Packaging Reduces Footprint Area

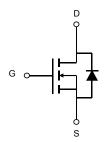


RoHS

APPLICATIONS

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial





Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	v	
	T _C = 25 °C		7.2 ^a		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	6.3 ^a		
Continuous Brain Carrent (1) = 100 °C)	T _A = 25 °C	ט' [3.3 ^{a, b, c}		
	T _A = 70 °C	1	2.1 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	29		
Continuous Source-Drain Diode Current	T _C = 25 °C		7.2 ^a		
	T _A = 25 °C	I _S	3.5 ^{b, c}		
	T _C = 25 °C		2.6		
Maximum Power Dissipation	T _C = 70 °C	P _D	1.16	w	
Maximum Fower Dissipation	T _A = 25 °C] '' [1.2 ^{b, c}	VV	
	T _A = 70 °C	1	0.5 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	42	60	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.8	8.9	O/VV

Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. The DFN2X2 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

Rev. 1.0 1

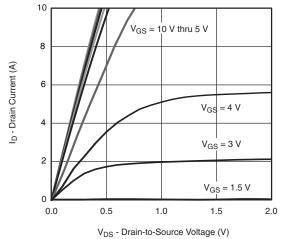
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		23			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	- I _D = 250 μA		- 5.5		mV/°C	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1.0		2.5	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 5	μΑ	
7 0		V _{DS} = 24 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55 °C			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	25			Α	
_	_	V _{GS} = 10 V, I _D = 8 A		19	23		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 5 A		23	28	mΩ	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 24 V, I _D = 8 A		30		S	
Dynamic ^b							
Input Capacitance	C _{iss}		T T	510	1		
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		77		pF	
Reverse Transfer Capacitance	C _{rss}			51			
·		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 8 A		9			
Total Gate Charge	Q_g			7		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5 \text{ A}$		1.8			
Gate-Drain Charge	Q _{gd}			1.5		1	
Gate Resistance	R _g	f = 1 MHz		2.9		Ω	
Turn-On Delay Time	t _{d(on)}			8			
Rise Time	t _r	V 45V 5 4 6		10		1	
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 15 \text{ V}, R_L = 1 \Omega$ $I_D \cong 8 \text{ A}, V_{GEN} = 10 \text{ V}, R_q = 1 \Omega$		25		1	
Fall Time	t _f	$ID = 0 A$, $VGEN - 10 V$, $II_g - 1 S2$		7		1	
Turn-On Delay Time	t _{d(on)}			12		ns	
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_1 = 1 \Omega$		17			
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 13 \text{ V, } R_L = 132$ $I_D \cong 5 \text{ A, } V_{GEN} = 4.5 \text{ V, } R_q = 1 \Omega$		37			
Fall Time	t _f			11		1	
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			7.2	_	
Pulse Diode Forward Current	I _{SM}				29	A	
Body Diode Voltage	V_{SD}	I _S = 1 A, V _{GS} = 0 V		0.7	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			23	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L = 9 A dl/dt = 100 A/up T = 25 °C		9	18	nC	
Reverse Recovery Fall Time	t _a	$I_F = 8 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		8			
Reverse Recovery Rise Time	t _b			10		ns	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

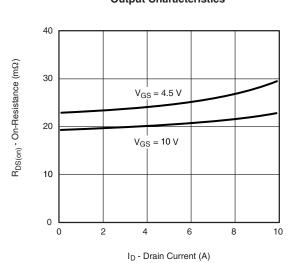
Notes: a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.



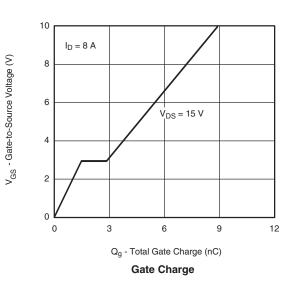
TYPICAL CHARACTERISTIC (25 °C, unless otherwise noted)

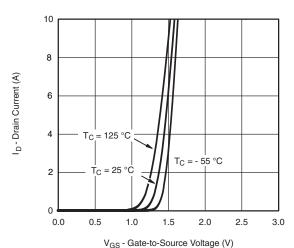


Output Characteristics

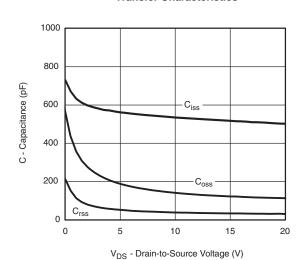


On-Resistance vs. Drain Current and Gate Voltage

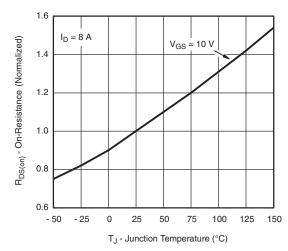




Transfer Characteristics



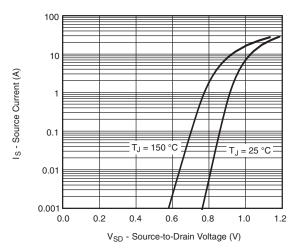
Capacitance



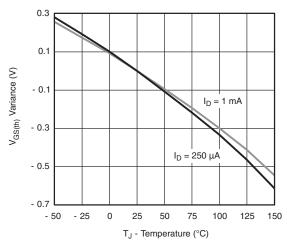
On-Resistance vs. Junction Temperature



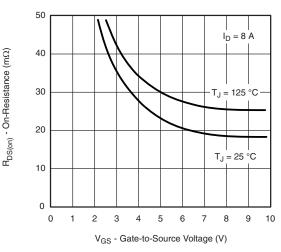
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



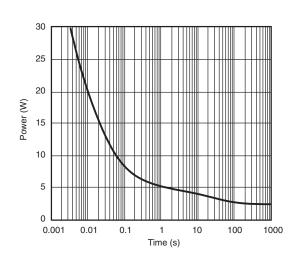
Source-Drain Diode Forward Voltage



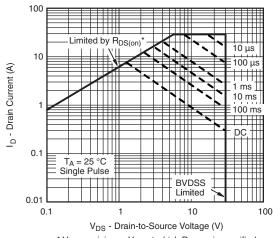
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)

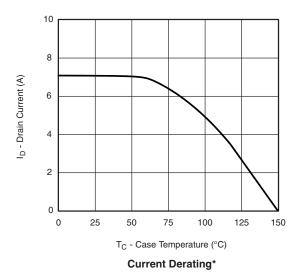


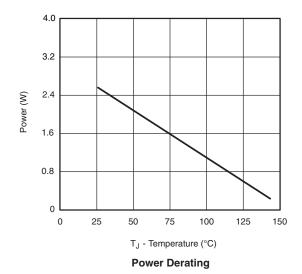
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

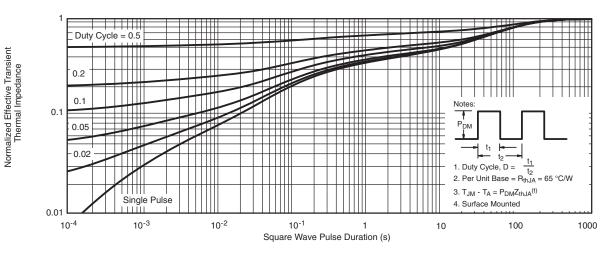




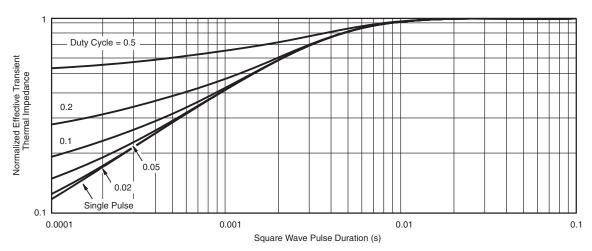
 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max.)}$ = 150 $^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

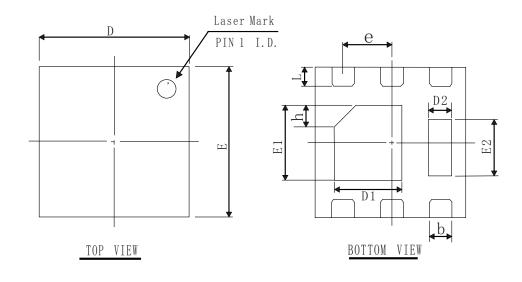


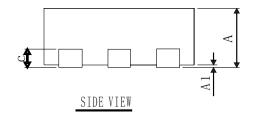
Normalized Thermal Transient Impedance, Junction-to-Case





DFN 2X2 PACKAGE OUTLINE





COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.60	0.75	0.90
A 1	0.00	0.02	0.10
b	0.15	0.25	0.40
D	1.80	2.00	2.25
Е	1.80	2.00	2.25
D1	0.70	0.90	1.10
E 1	0.75	1.00	1.20
D2	0.15	0.30	0.45
E2	0.45	0.75	0.95
L	0.15	0.25	0.40
h	0.15	0.25	0.40
С	0. 203 REF		
е	0. 65 BSC		

Other thickness dimensions are as follows

A	0.50	0.55	0.60
A	0.40	0.45	0.50

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